SuperMOS – SOP8 -30V BV_{DSS}, 15mΩ $R_{DS(on)}$, P-channel MOSFET

1. Description

The AO4805 is P-Channel enhancement MOS Field Effect Transistor. Uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. Device is suitable for use in DC-DC conversion, power switch and charging circuit. Standard Product AO4805 is Pb-free.

2. Features

- -30V, $R_{DS(ON)}$=15mΩ(TYP.) @V_{GS}=-10V
  $R_{DS(ON)}$=19mΩ(TYP.) @V_{GS}=-4.5V
  $R_{DS(ON)}$=19mΩ(MAX.) @V_{GS}=-20V
- Fast Switching
- High density cell design for low $R_{DS(on)}$
- Material: Halogen free
- Reliable and rugged
- Avalanche Rated
- Low leakage current

3. Applications

- PWM applications
- Load switch
- Power management in portable/desktop PCs
- DC/DC conversion

100% UIS TESTED!

4. Ordering Information

Part Number	Package	Marking	Material	Packing	Quantity per reel	Flammability Rating	Reel Sizes
AO4805	SOP8	ES4805/lot	Halogen free	Tape & Reel	3,000 PCS	UL 94V-0	13 inches

Table-1 Ordering information

5. Pin Configuration and Functions

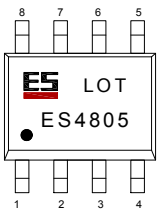
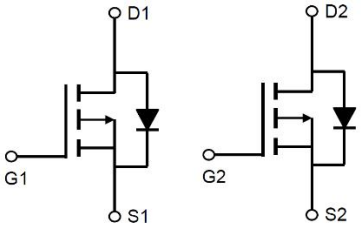
Pin	Function	Outline	Circuit Diagram
2	Gate1		
1	Source1		
7/8	Drain1		
4	Gate2		
3	Source2		
5/6	Drain2		

Table-2 Pin configuration

6. Specification

Absolute Maximum Rating & Thermal Characteristics

Ratings at 25 ℃ ambient temperature unless otherwise specified.

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		BV_{DSS}	-30	V
Gate-Source Voltage		V_{GS}	±25	V
Continuous Drain Current	T_A=25°C	I_D	-10	A
	T_A=75°C		-8	
Maximum Power Dissipation	T_A=25°C	P_D	3.2	W
	T_A=75°C		1.9	
Pulsed Drain Current		I_{DM}	-40	A
Avalanche Current, Single Pulsed [a]		I_{AS}	-21	A
Avalanche Energy, Single Pulsed [a]		E_{AS}	66	mJ
Operating Junction Temperature		T_J	150	°C
Storage Temperature Range		T_{stg}	-55 to +150	°C

Thermal resistance ratings

Single Operation				
Parameter	Symbol	Typical	Maximum	Unit
Junction-to-Ambient Thermal Resistance	$R_{\theta JA}$	32	40	°C/W
Junction-to-Lead Thermal Resistance	$R_{\theta JL}$	20	28	

Note:

a:Tj=25℃, V_{DD}=-30V, V_G=-10V, L=0.3mH, Rg=25Ω

Electrical Characteristics

At TA = 25℃ unless otherwise specified

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V, I_D=-250uA	-30			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS}=0V, V_{DS}=-30V			-1	uA
Gate-to-source Leakage Current	I_{GSS}	V_{GS}=±25V, V_{DS}=0V			±100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS}=V_{DS}, I_D=-250uA	-1.0	-1.5	-2.0	V
Drain-to-source On-resistance	$R_{DS(on)}$	V_{GS}=-20V, I_D=-9A			19	mΩ
		V_{GS}=-10V, I_D=-8A		15	22	
		V_{GS}=-4.5V, I_D=-5A		19	28	
CHARGES, CAPACITANCES AND GATE RESISTANCE						
Input Capacitance	C_{ISS}	V_{GS}=0V, V_{DS} =-15V f=1MHz		2060	2600	pF
Output Capacitance	C_{OSS}			370		
Reverse Transfer Capacitance	C_{RSS}			300		
Gate Resistance	R_g	f=1MHZ		2.5		Ω
Total Gate Charge	$Q_{G(TOT)}$	V_{GS}=-10V, V_{DS}=-15V I_D=-8A		30	40	nC
Gate-to-Source Charge	Q_{GS}			4.5		
Gate-to-Drain Charge	Q_{GD}			10		
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	$t_{d(ON)}$	V_{GS}=-10V, V_{DS}=-15V R_L=1Ω, R_G=3Ω		11		ns
Rise Time	t_r			9.5		
Turn-Off Delay Time	$t_{d(OFF)}$			25		
Fall Time	t_f			12		
BODY DIODE CHARACTERISTICS						
Forward Voltage	V_{SD}	V_{GS}=0V, I_{SD}=-8A		-0.75	-1.5	V

7. Typical Characteristic

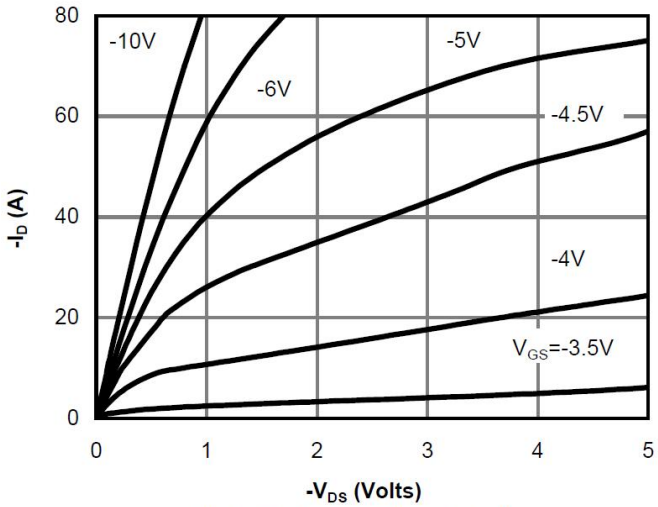


Fig 1: On-Region Characteristics

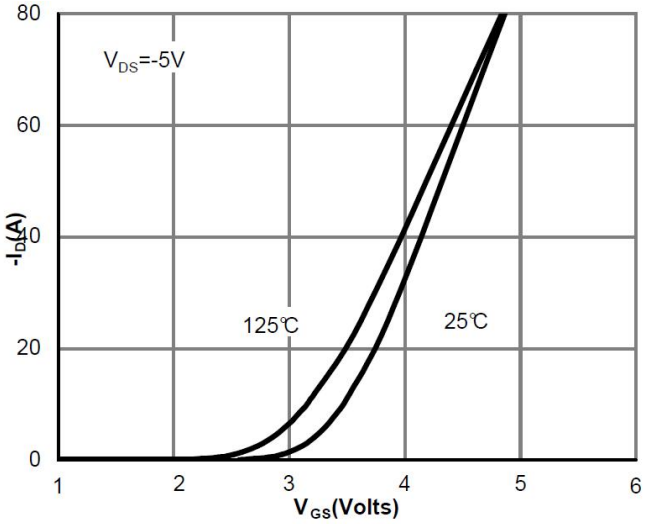


Figure 2: Transfer Characteristics

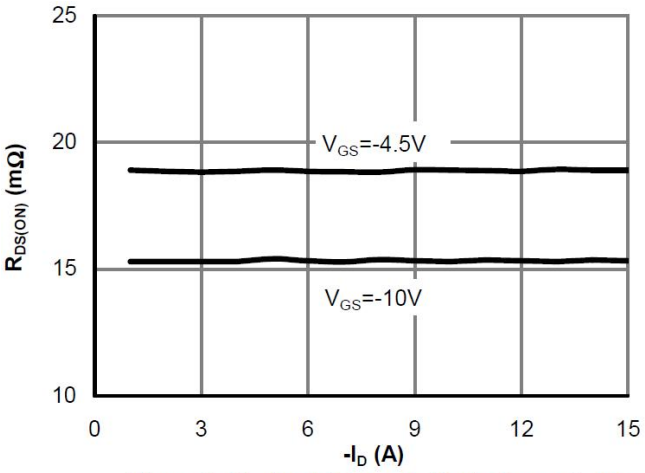


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

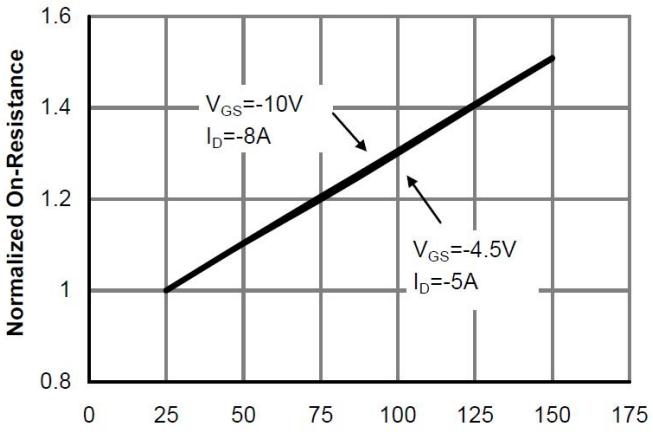


Figure 4: On-Resistance vs. Junction Temperature

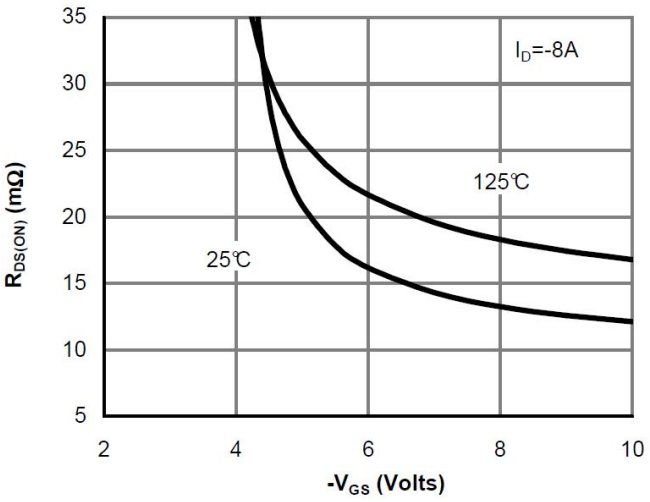


Figure 5: On-Resistance vs. Gate-Source Voltage

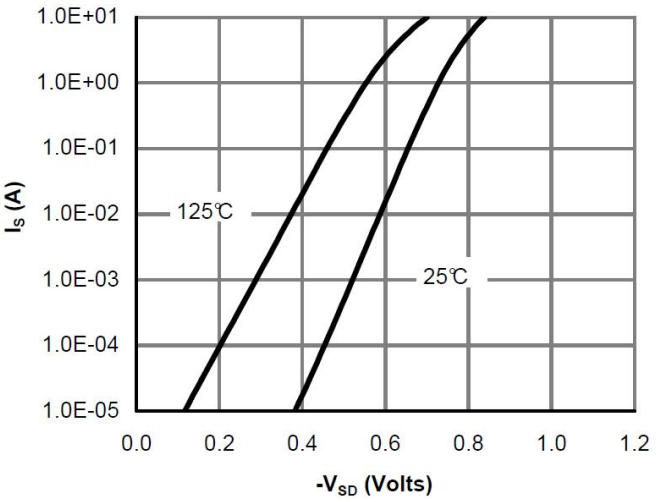


Figure 6: Body-Diode Characteristics

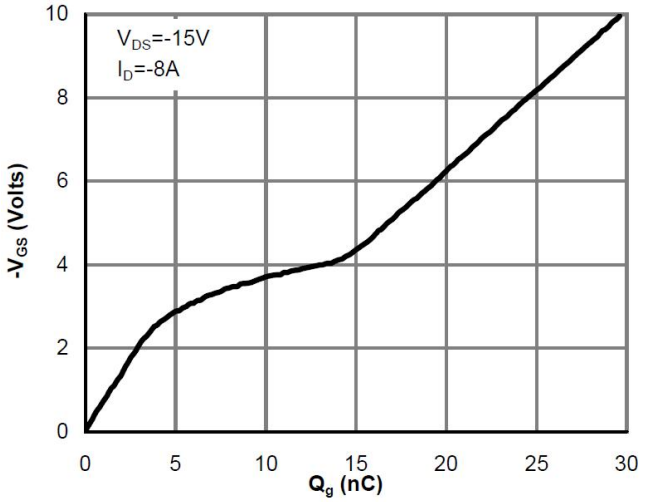


Figure 7: Gate-Charge Characteristics

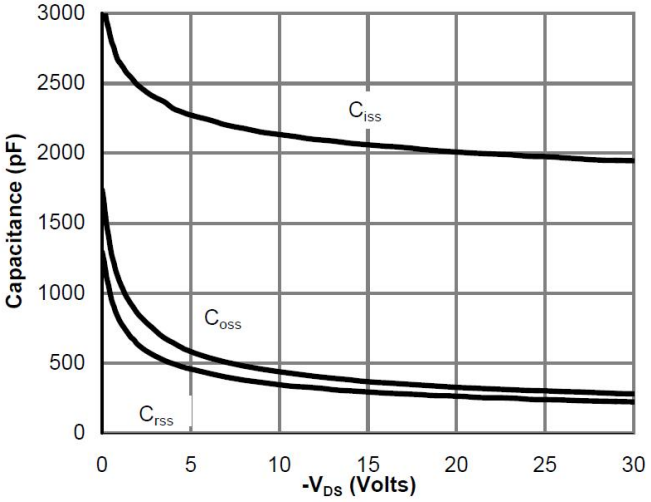


Figure 8: Capacitance Characteristics

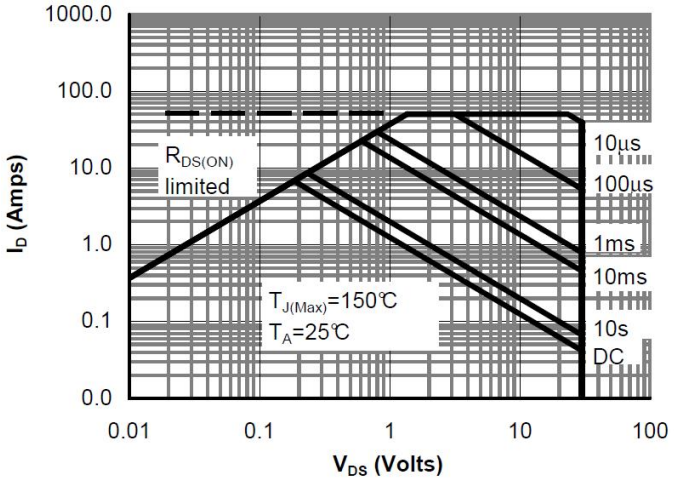


Figure 9: Maximum Forward Biased Safe Operating Area

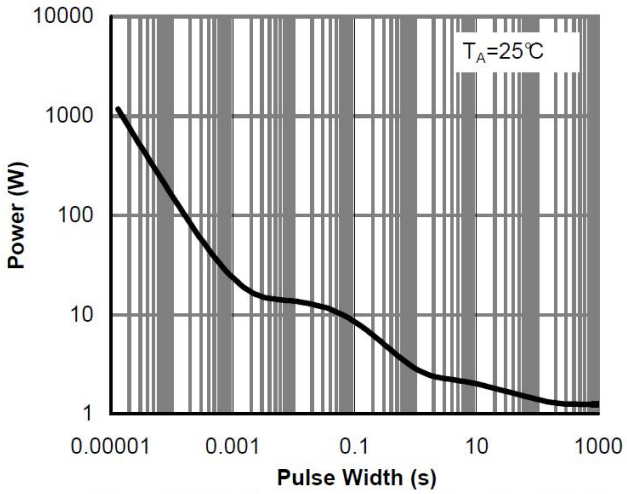


Figure 10: Single Pulse Power Rating Junction-to-Ambient

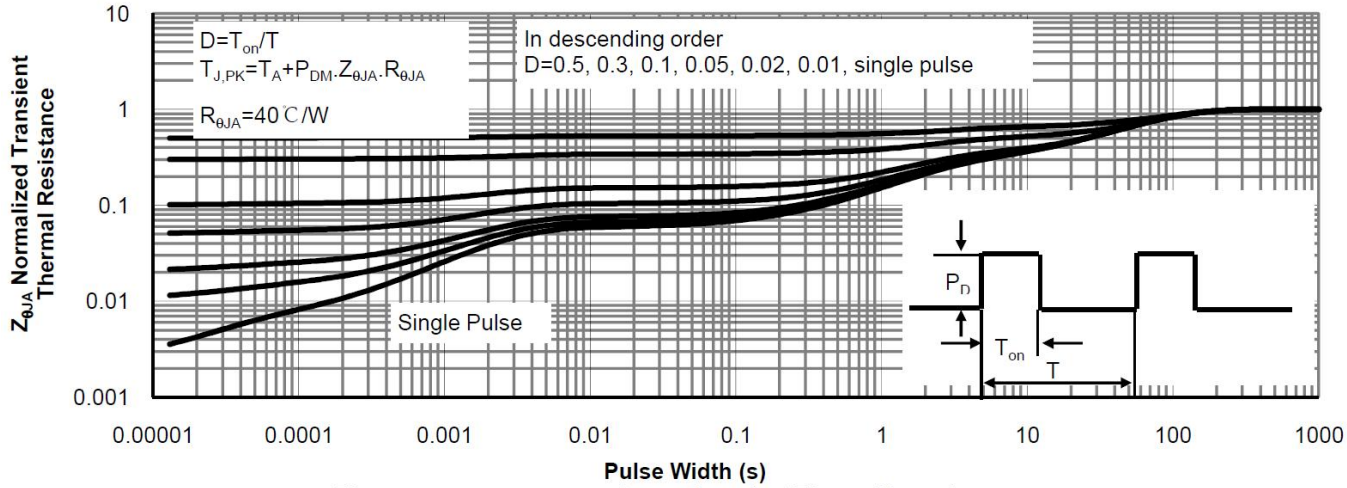
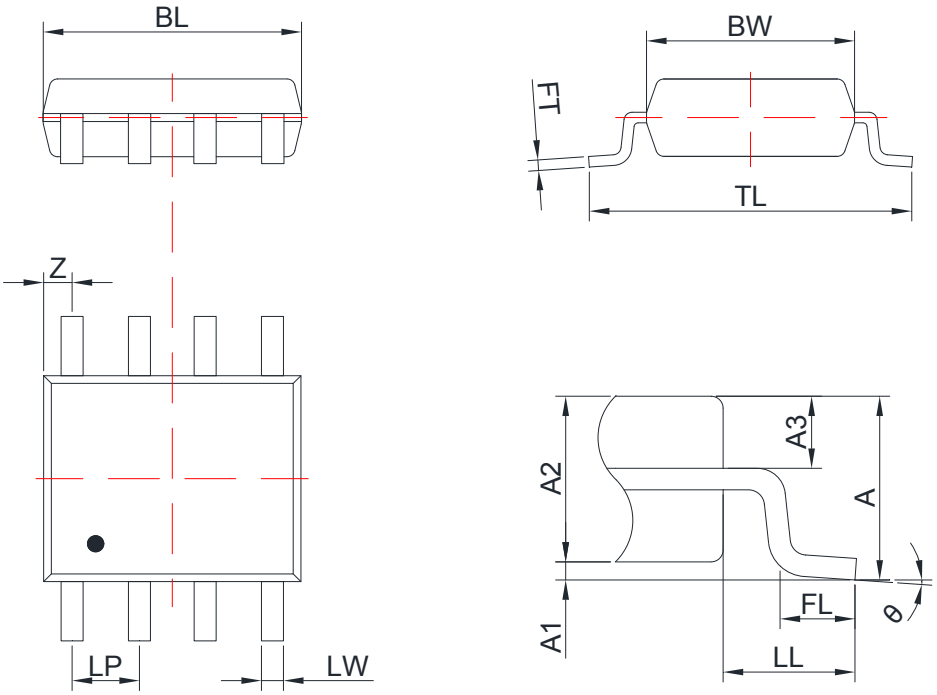


Figure 11: Normalized Maximum Transient Thermal Impedance

8. Dimension and Patterns (SOP8)



COMMON DIMENSIONS: UNITS OF MEASURE=MILLIMETER

Symbol	Dimensions		Symbol	Dimensions	
	Min.	Max.		Min.	Max.
A	1.75		FL	0.50	0.80
A1	0.05	0.15	LP	1.25	1.30
A2	1.40	1.50	LL	1.1 BSC	
A3	0.623 BSC		LW	0.38	0.43
BL	4.80	5.00	TL	5.90	6.10
BW	3.70	4.10	Z	0.54	
FT	0.20	0.21	θ	0°	8°

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